

## CORRECTION

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[View Journal](#) | [View Issue](#)Cite this: *J. Mater. Chem. C*, 2020, **8**, 5293**Correction: High-performance optoelectronic memory based on bilayer MoS<sub>2</sub> grown by Au catalyst**Fengyou Yang,<sup>ab</sup> Shengyao Chen,<sup>ac</sup> Huimin Feng,<sup>ab</sup> Cong Wang,<sup>d</sup> Xiaofeng Wang,<sup>ab</sup> Shu Wang,<sup>ab</sup> Zhican Zhou,<sup>ac</sup> Bo Li,<sup>ab</sup> Lijun Ma,<sup>a</sup> Haiguang Yang,<sup>ab</sup> Yong Xie<sup>e</sup> and Qian Liu<sup>\*abc</sup>

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[rsc.li/materials-c](https://rsc.li/materials-c)Correction for 'High-performance optoelectronic memory based on bilayer MoS<sub>2</sub> grown by Au catalyst' by Fengyou Yang *et al.*, *J. Mater. Chem. C*, 2020, **8**, 2664–2668.

The author regret an error in Fig. 4d of the published article; the corrected version of Fig. 4d is shown here. The rest of Fig. 4 and the caption are unchanged.

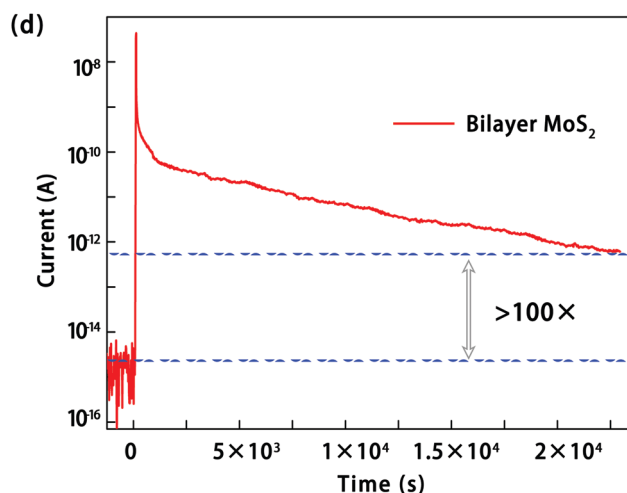


Fig. 4 (d) The retention time property of the bilayer MoS<sub>2</sub> optoelectronic memory.

Please note that these changes do not affect the results and conclusions reported in the article.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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